



500V Super-junction Power MOSFET

Description

500V Super-junction Power MOSFET

Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The deep trench SJ MOSFET provide an extremely low switching, commutation and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler, designed by Wuxi Unigroup Microelectronics Company.

Features

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

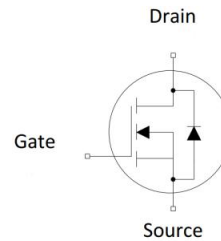
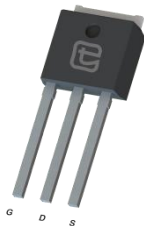
Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger

TO-252



TO-251



Device Marking and Package Information

Device	Package	Marking
TPD50R360D	TO-252	50R360D
TPU50R360D	TO-251	50R360D

Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	550	V
$R_{DS(on),max}$	0.36	Ω
$Q_{g,typ}$	12.8	nC
I_D	7	A
$I_{D,pulse}$	21	A
$E_{OSS} @ 400V$	2.05	μJ



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted				
Parameter		Symbol	Values	Unit
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	7	A
	$T_C = 100^\circ\text{C}$		4	
Pulsed Drain Current	(note1)	$I_{D,pulse}$	21	A
Gate-Source Voltage		V_{GSS}	$\pm 30\text{V}$	V
Single Pulse Avalanche Energy	(note2)	E_{AS}	45	mJ
Repetitive Avalanche Energy	(note2)	E_{AR}	0.28	mJ
Avalanche Current		I_{AR}	3	A
MOSFET dv/dt Ruggedness, $V_{DS} = 0 \dots 480\text{V}$		dv/dt	50	V/ns
Power Dissipation For TO-252, TO-251		P_D	62.5	W
Continuous Diode Forward Current		I_S	7	A
Diode Pulsed Current	(note1)	$I_{S,pulse}$	21	
Reverse Diode dv/dt	(note3)	dv/dt	5	V/ns
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance For TO-252, TO-251			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	2	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	



Electrical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	500	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{DS} = 500V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	--	4.0	V
Drain-Source On-State-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3A$	--	0.29	0.36	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	550	--	μF
Output Capacitance	C_{oss}		--	23.71	--	
Reverse Transfer Capacitance	C_{rss}		--	0.68	--	
Total Gate Charge	Q_g	$V_{DD} = 400V, I_D = 7A,$ $V_{GS} = 10V$	--	12.8	--	nC
Gate-Source Charge	Q_{gs}		--	2.2	--	
Gate-Drain Charge	Q_{gd}		--	5.6	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 7A,$ $R_G = 25\Omega$	--	34.7	--	ns
Turn-on Rise Time	t_r		--	9	--	
Turn-off Delay Time	$t_{d(off)}$		--	62.8	--	
Turn-off Fall Time	t_f		--	19.25	--	
Drain-Source Body Diode Characteristics						
Body Diode Forward Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 7A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 400V, I_S = 3A,$ $di_F/dt = 100\text{A}/\mu\text{s}$	--	139.6	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.906	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	12.9	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 10\text{mH}, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Identical low side and high side switch with identical R_G



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

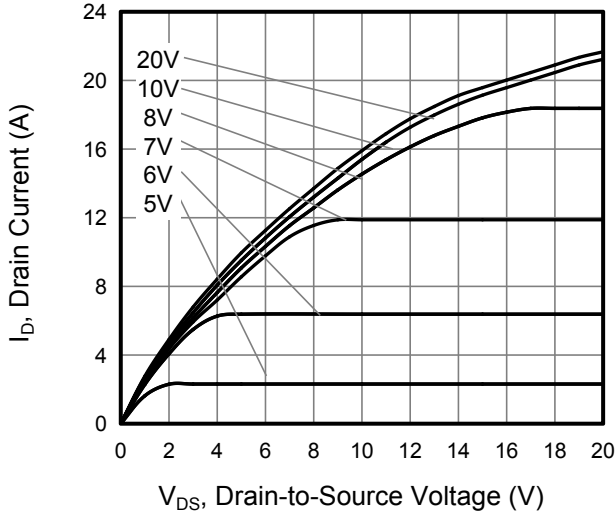


Figure 2. Transfer Characteristics

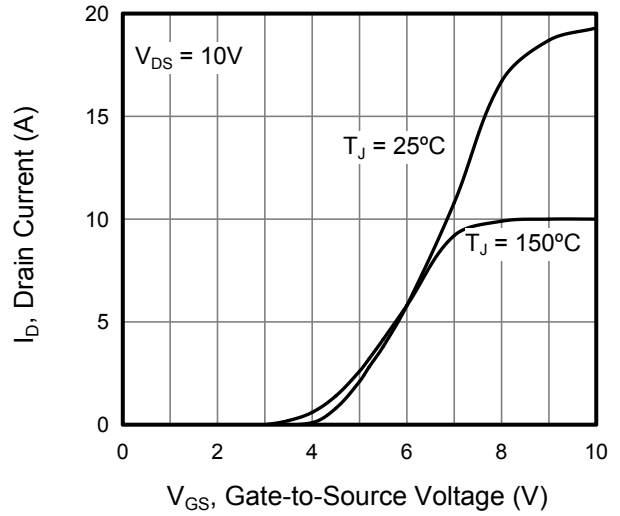


Figure 3. On-Resistance vs. Drain Current

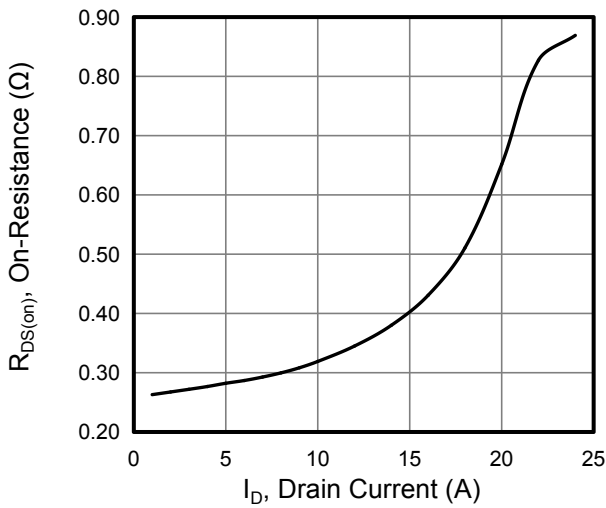


Figure 4. Capacitance

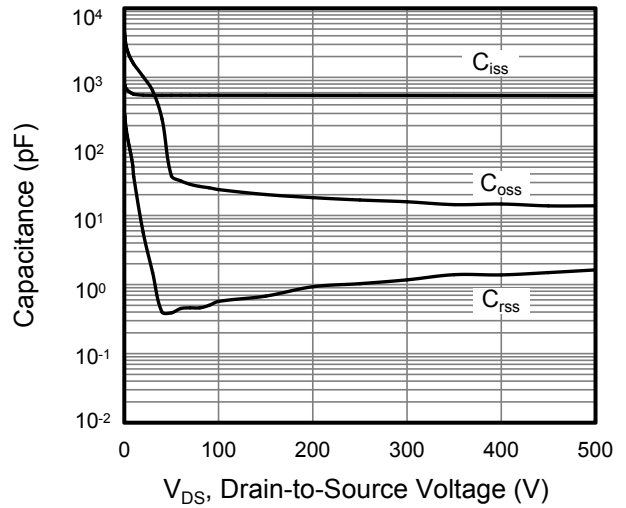


Figure 5. Gate Charge

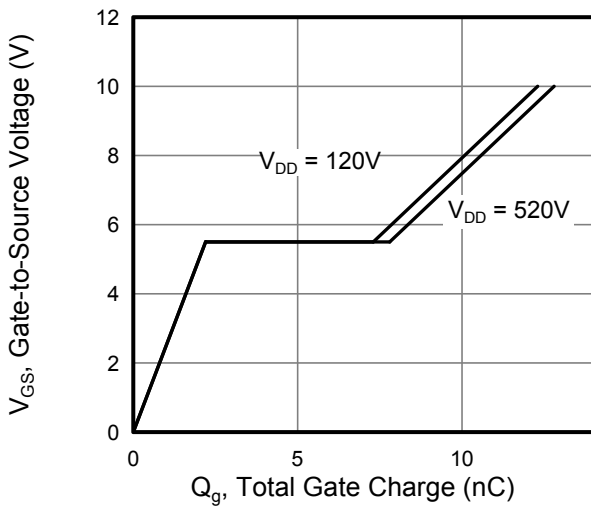


Figure 6. Body Diode Forward Voltage

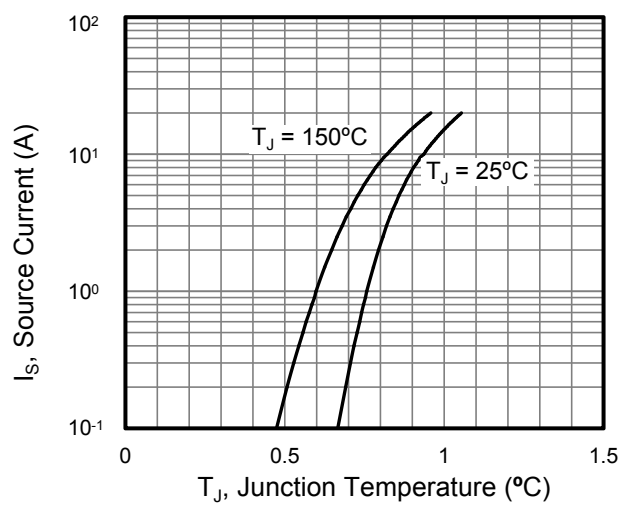




Figure 7. On-Resistance vs. Temperature

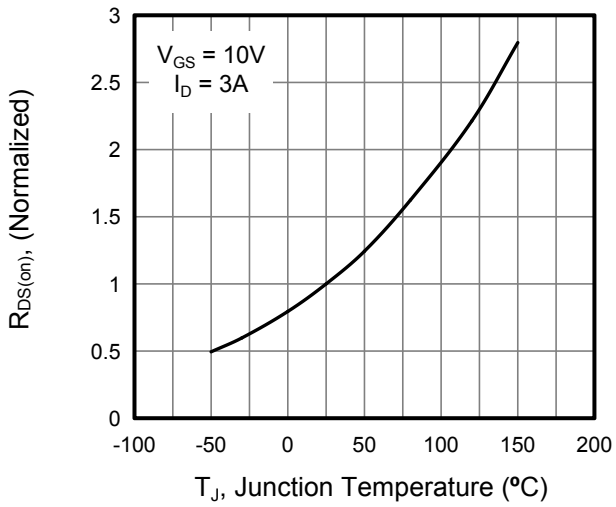


Figure 8. Breakdown voltage vs. Junction Temperature

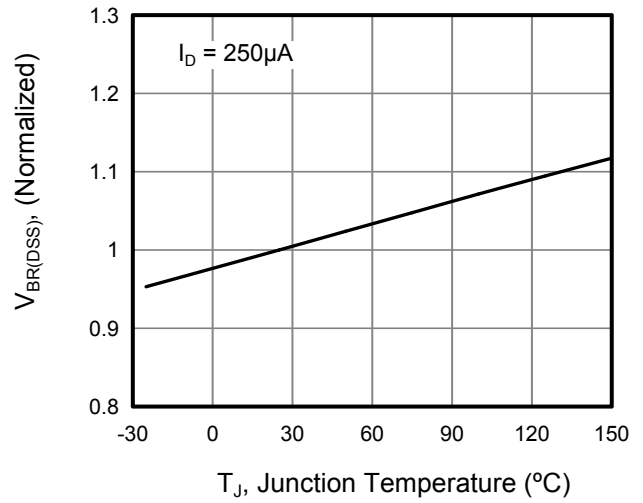


Figure 9. Transient Thermal Impedance For TO-252/TO-251

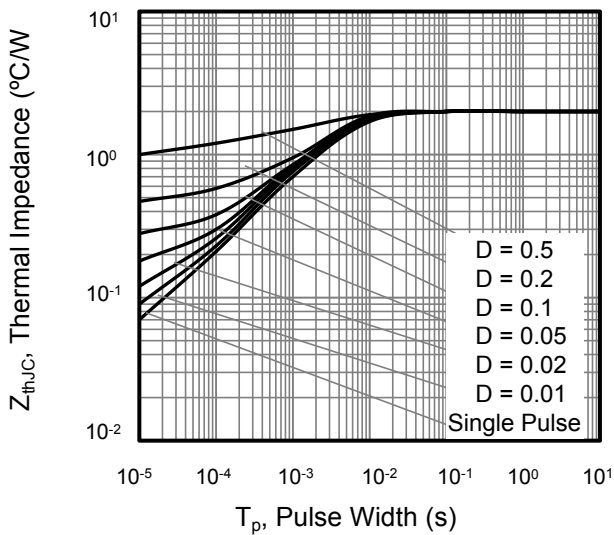


Figure 10. Safe Operation Area For TO-252/TO-251

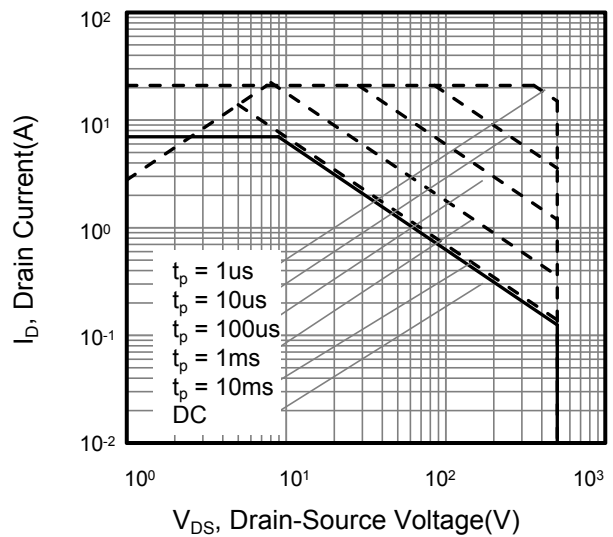


Figure 11. Typ. Coss Stored Energy

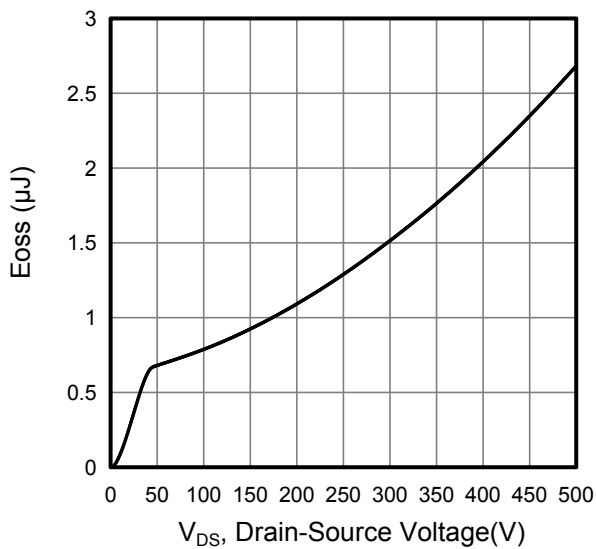




Figure A: Gate Charge Test Circuit and Waveform

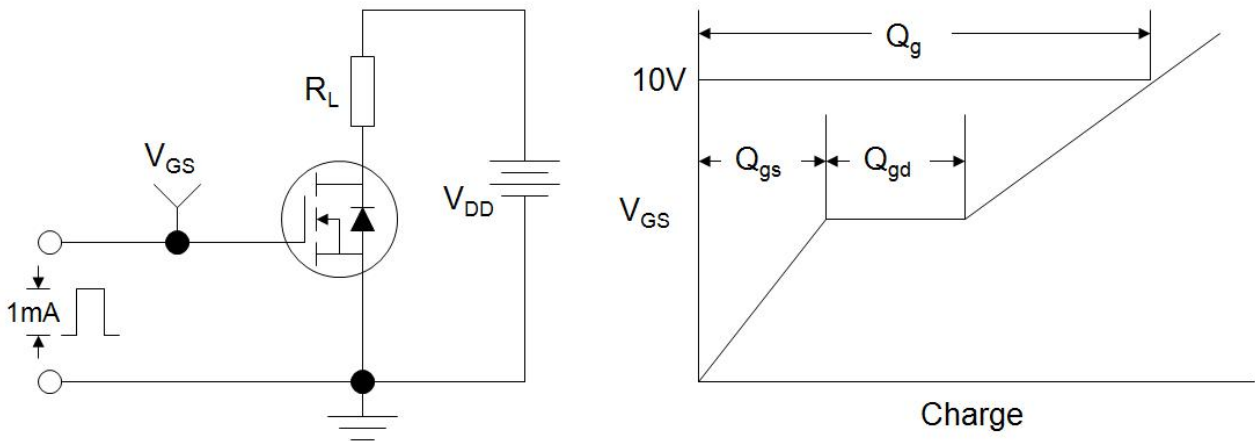


Figure B: Resistive Switching Test Circuit and Waveform

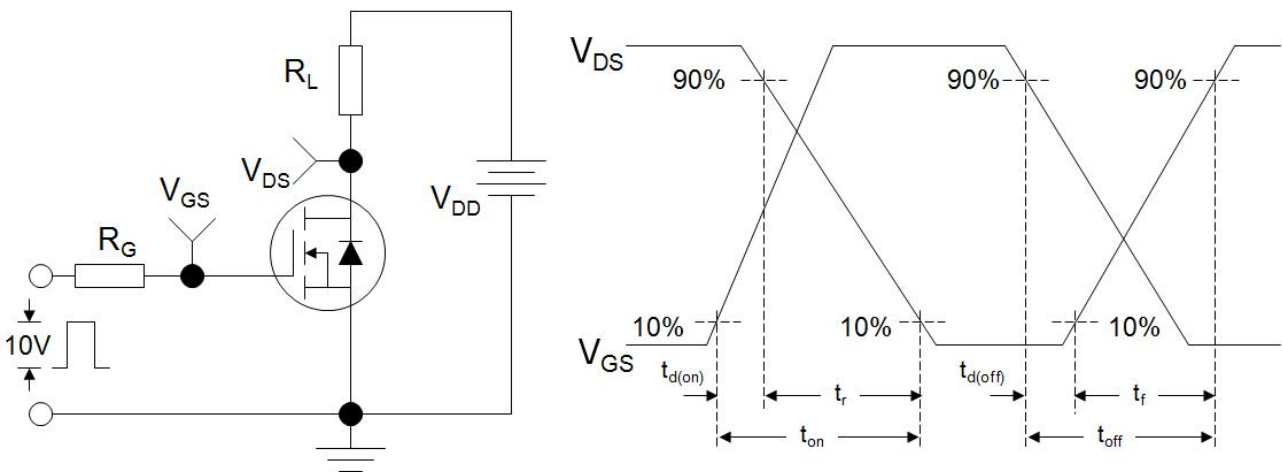
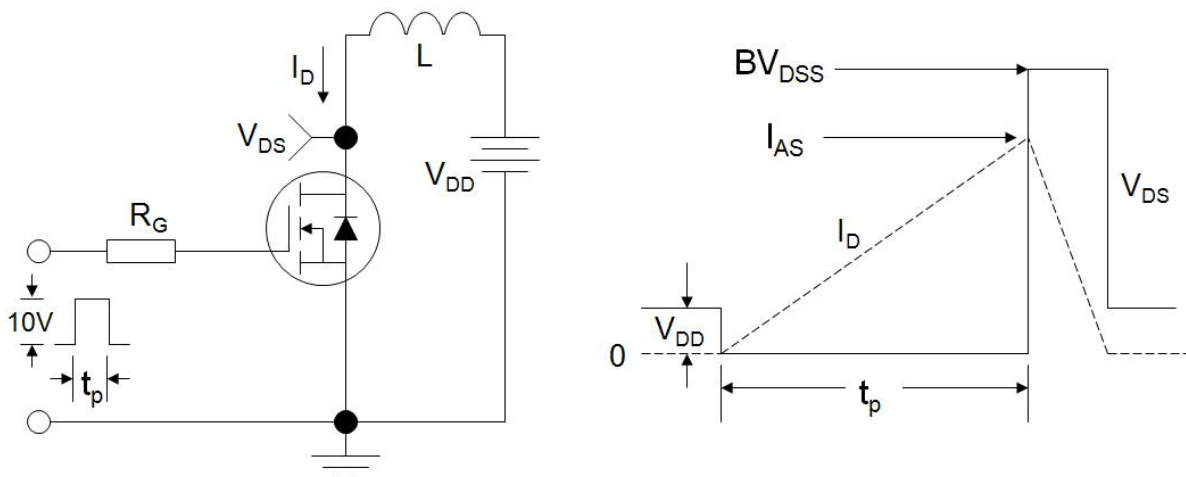
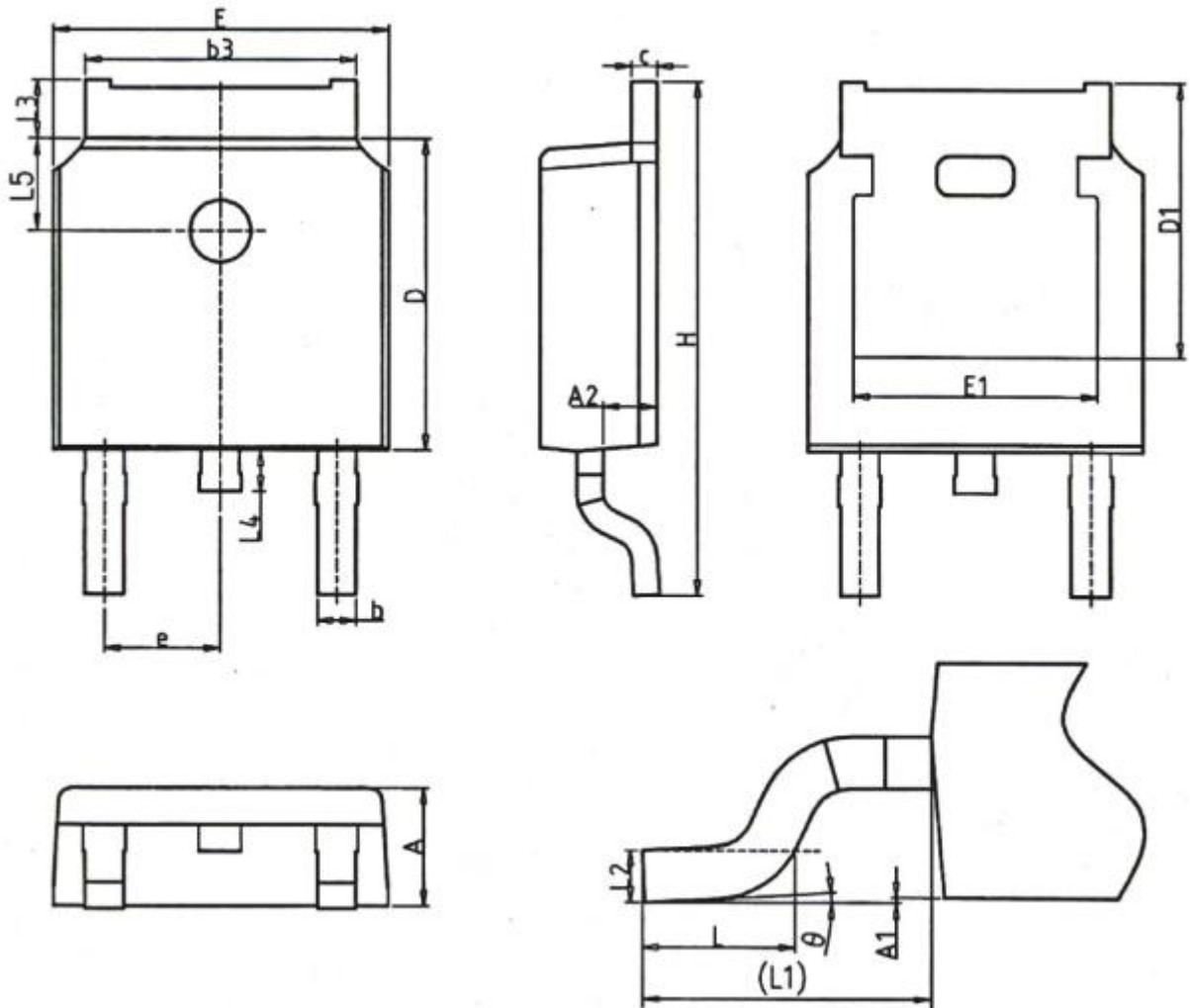


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-252 (封装厂 H)

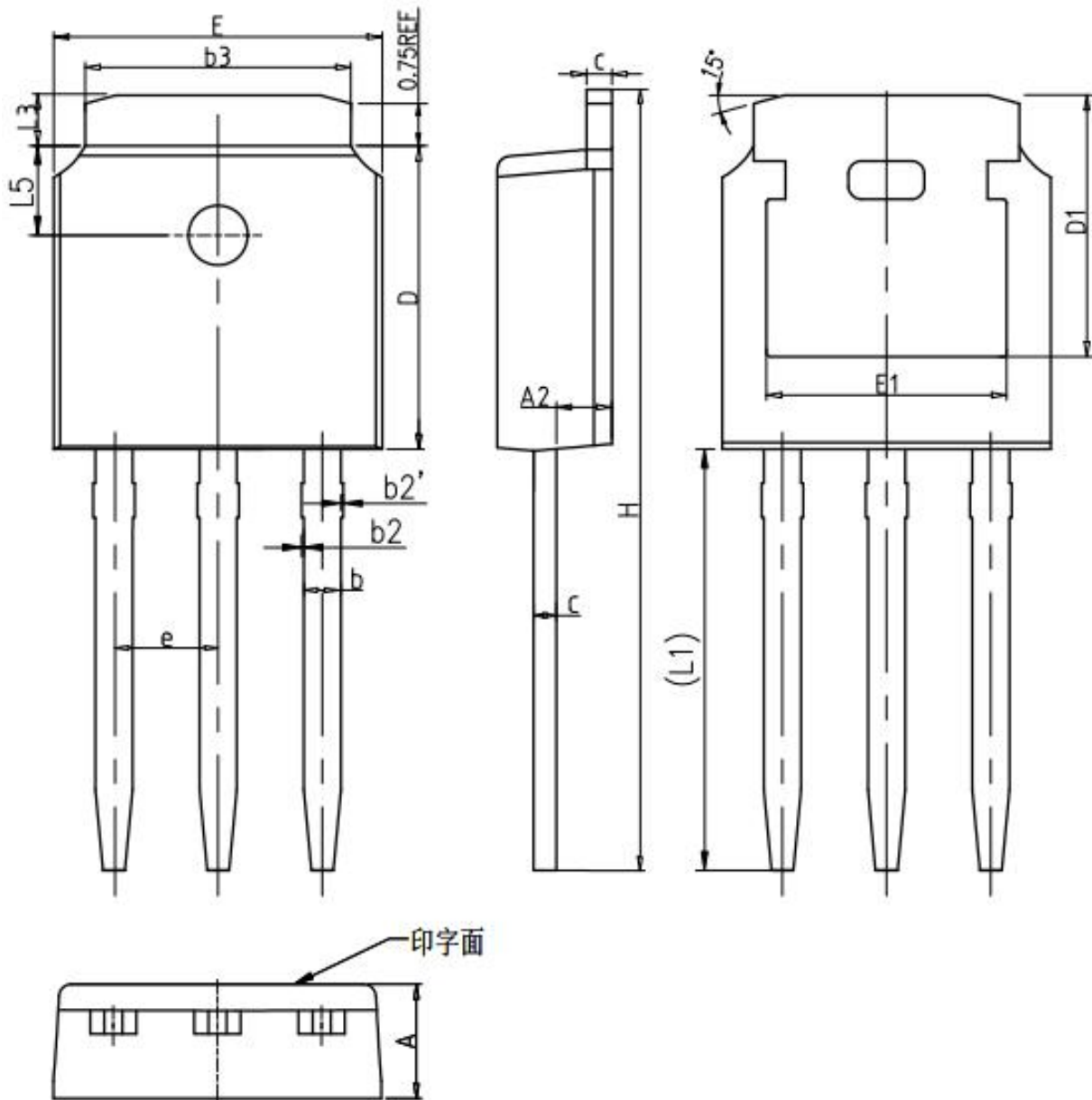


Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.73
E1	4.63	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.286 BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.51 BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
θ	0°	-	8°



TO-251 (封装厂 H)



Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22

Unit:mm			
Symbol	Min.	Nom	Max.
D1	5.30 REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286 BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95



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